

# 2SK2084(L), 2SK2084(S)

# Silicon N Channel MOS FET

REJ03G0995-0200

(Previous: ADE-208-1342)

Rev.2.00 Sep 07, 2005

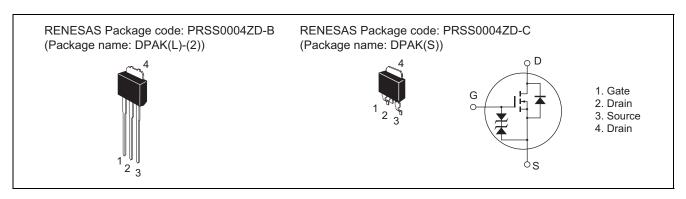
#### **Application**

High speed power switching

#### **Features**

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source
- Suitable for switching regulator, DC DC converter

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	20	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	I <sub>D</sub>	7	A
Drain peak current	I <sub>D(pulse)</sub> *1	28	A
Body to drain diode reverse drain current	I <sub>DR</sub>	7	A
Channel dissipation	Pch*2	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$ 10  $\mu$ s, duty cycle  $\leq$  1 %

2. Value at Tc = 25°C

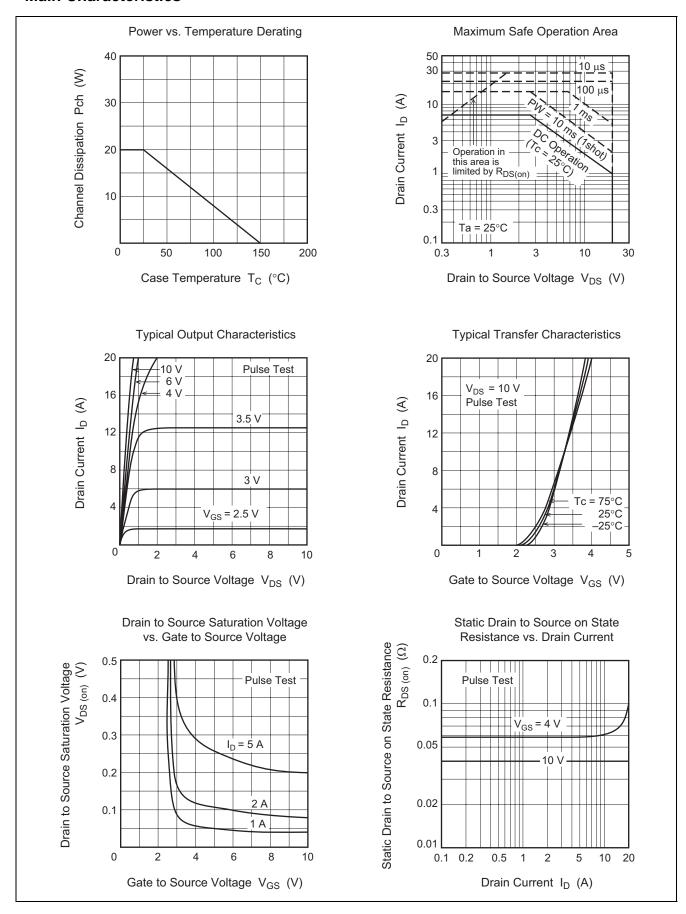
### **Electrical Characteristics**

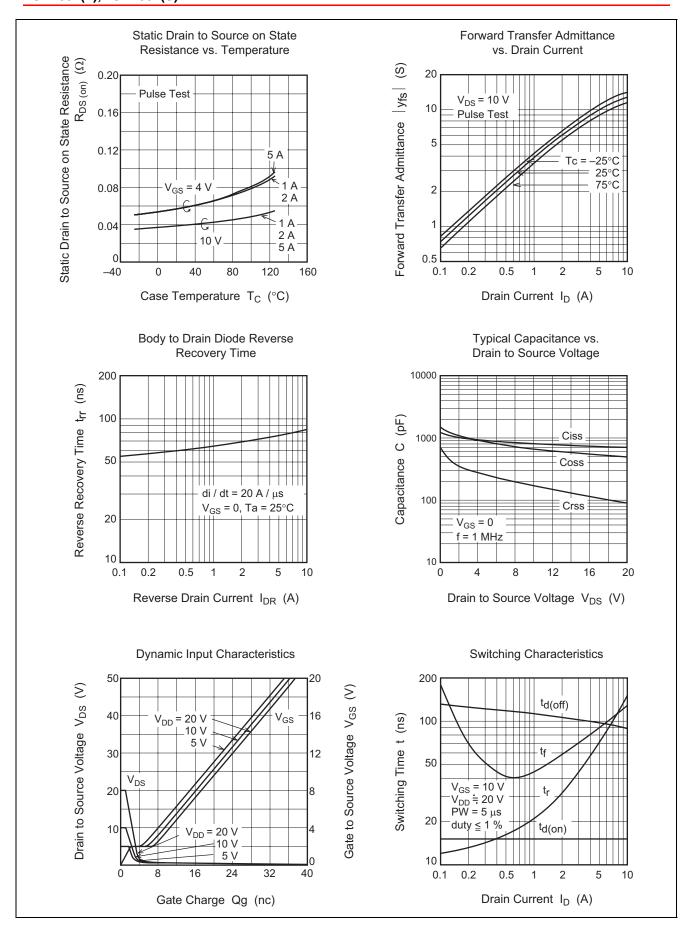
 $(Ta = 25^{\circ}C)$ 

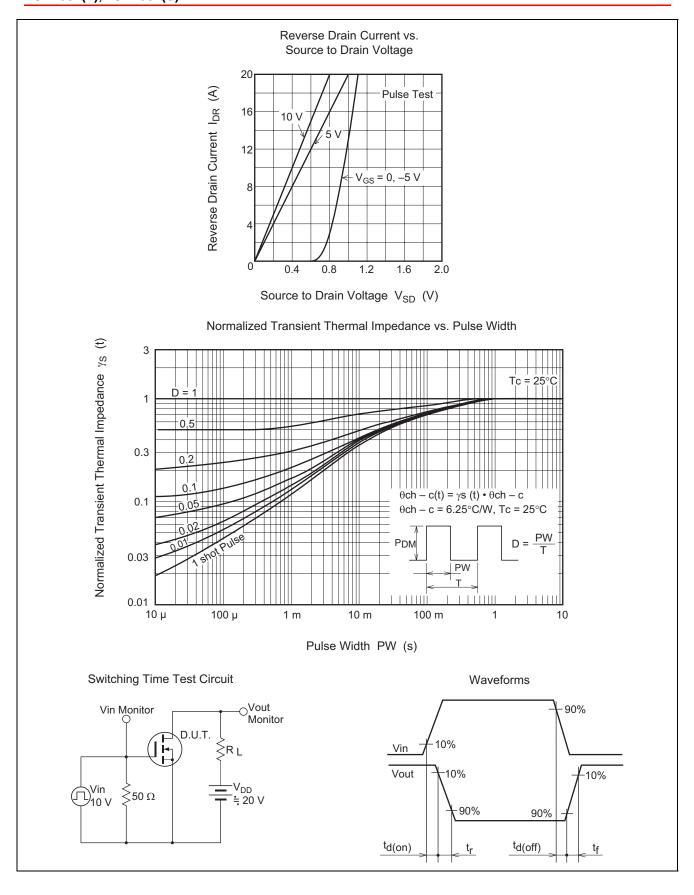
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	20	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	100	μΑ	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	_	2.5	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state	R <sub>DS(on)</sub>	_	0.04	0.053	Ω	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$
resistance		_	0.058	0.075	Ω	$I_D = 4 \text{ A}, V_{GS} = 4 \text{ V}^{*3}$
Forward transfer admittance	y <sub>fs</sub>	5	9	_	S	$I_D = 4 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$
Input capacitance	Ciss	_	800	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	680	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	165	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	15	_	ns	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t <sub>r</sub>	_	60	_	ns	$R_L = 5 \Omega$
Turn-off delay time	t <sub>d(off)</sub>	_	100	_	ns	
Fall time	t <sub>f</sub>	_	80	_	ns	
Body to drain diode forward voltage	$V_{DF}$	_	0.9	_	V	$I_F = 7 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery	t <sub>rr</sub>	_	80	_	ns	$I_F = 7 \text{ A}, V_{GS} = 0,$
time						$di_F / dt = 20 A / \mu s$

Note: 3. Pulse Test

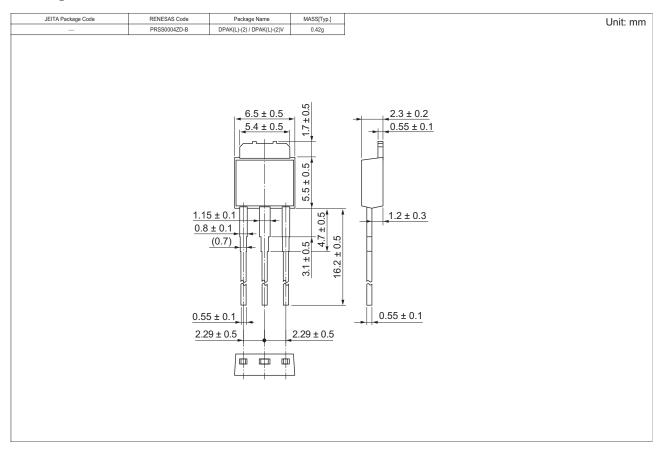
#### **Main Characteristics**

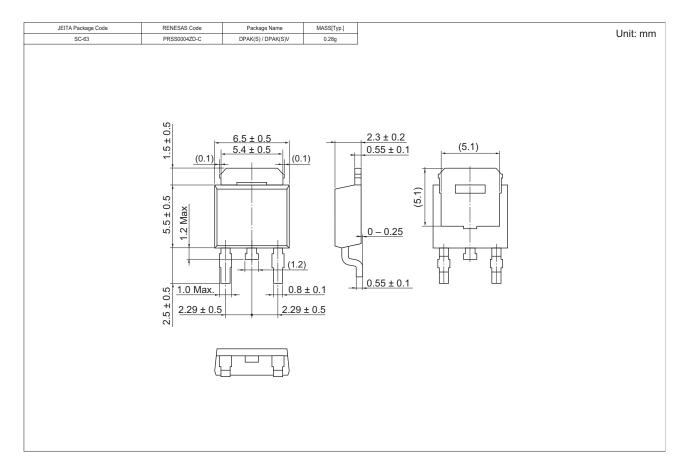






## **Package Dimensions**





## **Ordering Information**

Part Name	Quantity	Shipping Container
2SK2084L-E	3000 pcs	Box (Sack)
2SK2084STL-E	3000 pcs	Taping

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